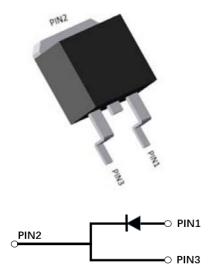


YJD106510BQG2Q

Silicon Carbide Schottky Diode

V _{RRM}	650V	
I _F (135°C)	14A	
Qc	30nC	



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- AEC-Q101 qualified
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: TO-263AC Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free
- Terminals: Tin plated leads
- Polarity: As marked

PARAMTETER SYMBOL UNIT VALUE D106510BQG2 Device marking code Reverse voltage (repetitive peak) V_{RRM} V 650 @ Tj=25°C Reverse voltage (Surge Peak) V 650 V_{RSM} @ T_i=25°C Reverse voltage (DC) V_{DC} V 650 @ T_i=25°C Continuous forward current @ Tc=25°C 30 Continuous forward current @ Tc=135°C I_{F} А 14 Continuous forward current @ Tc=154°C 10 Non-repetitive peak forward surge current А 70 IFSM @ T_c=25°C, tp=10ms, Half Sine Wave Power Dissipation@ Tc=25°C 136 W **P**_{TOT} Power Dissipation@ Tc=110°C 59 i²t Value@ Tc=25°C ,tp=10ms ∫ i²dt A²S 32 T_j ,T_{stg} °C -55 to +175 Operating junction and Storage temperature range

■Maximum Ratings (T_c=25[°]C Unless otherwise specified)

Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.
Forward voltage drop	V _F	v	I _F =10A, T _j =25°C	1.35	1.55
			I _F =10A, T _j =175°C	1.8	-
Reverse leakage current	I _R	μA	V _R =650V, T _j =25°C	0.5	25
			V _R =650V, T _j =175°C	2	-
Total capacitive charge	Qc	nC	V_R =400V, T _j =25°C , QC= \int_0^{VR} C(V)dV	30	-
Total capacitance	С	pF	V _R =0V, f=1MHZ	543	-
			V _R =200V, f=1MHZ	55	-
			V _R =400V, f=1MHZ	52	-
Capacitance Stored Energy	Ec	μJ	V _R =400V	3.7	-

■Thermal Characteristics (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	R _{øJ-C}	°C W	1.1

■Typical Characteristics

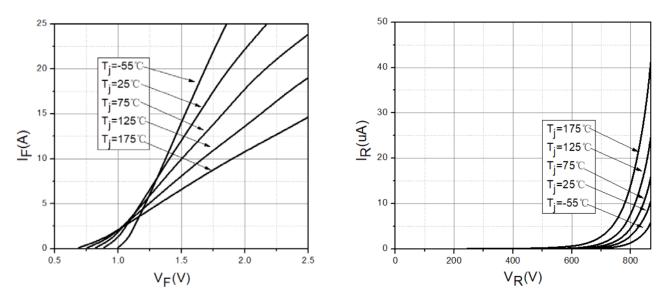


Figure 1. Forward Characteristics

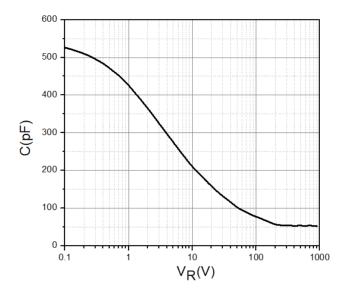
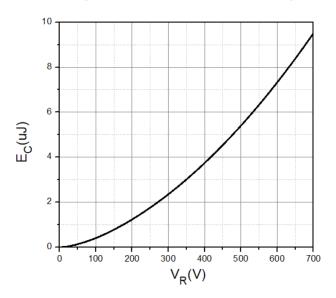
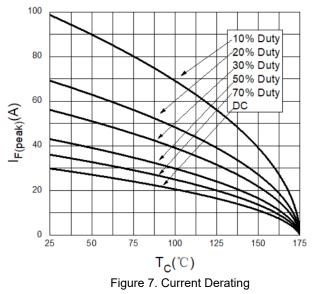


Figure 3. Capacitance vs. Reverse Voltage







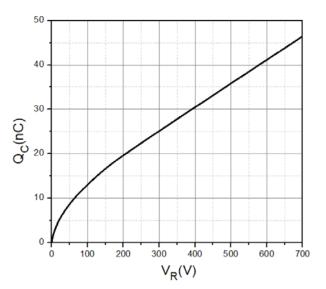
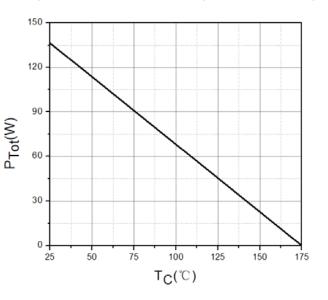
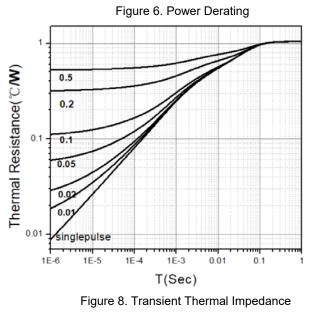


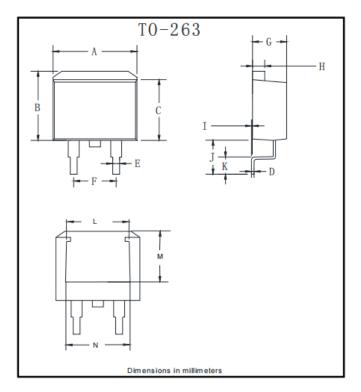
Figure 4. Total Capacitance Charge vs. Reverse Voltage







Outline Dimensions



TO-263					
Dim	Min	Max			
А	9.5	11.5			
В	9.7	10.5			
С	8.4	9.0			
D	0.28	0.64			
E	0.68	0.94			
F	4.55	5.6			
G	4.04	5.10			
Н	1.14	1.4			
I	0	0.2			
J	4.9	6.05			
K	1.79	2.79			
L	7.3	7.9			
М	6.2	6.8			
N	7.6	8.2			

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